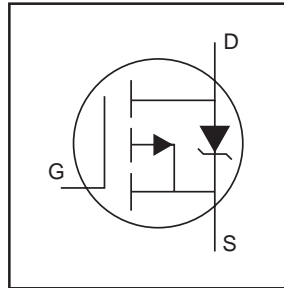


IRFR5305PbF

IRFU5305PbF

HEXFET® Power MOSFET

- Ultra Low On-Resistance
- Surface Mount (IRFR5305)
- Straight Lead (IRFU5305)
- Advanced Process Technology
- Fast Switching
- Fully Avalanche Rated
- Lead-Free

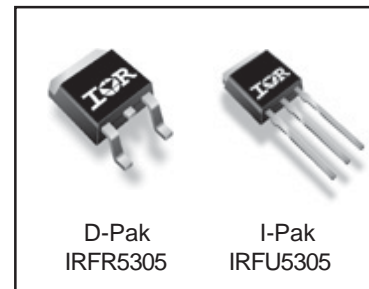


$V_{DSS} = -55V$
$R_{DS(on)} = 0.065\Omega$
$I_D = -31A$

### Description

Fifth Generation HEXFETs from International Rectifier utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. This benefit, combined with the fast switching speed and ruggedized device design that HEXFET® Power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in a wide variety of applications.

The D-Pak is designed for surface mounting using vapor phase, infrared, or wave soldering techniques. The straight lead version (IRFU series) is for through-hole mounting applications. Power dissipation levels up to 1.5 watts are possible in typical surface mount applications.



D-Pak  
IRFR5305

I-Pak  
IRFU5305

### Absolute Maximum Ratings

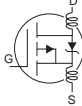
	Parameter	Max.	Units
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-31	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V$	-22	
$I_{DM}$	Pulsed Drain Current ①②	-110	
$P_D @ T_C = 25^\circ C$	Power Dissipation	110	W
	Linear Derating Factor	0.71	W/°C
$V_{GS}$	Gate-to-Source Voltage	$\pm 20$	V
$E_{AS}$	Single Pulse Avalanche Energy ②③	280	mJ
$I_{AR}$	Avalanche Current ①③	-16	A
$E_{AR}$	Repetitive Avalanche Energy ①	11	mJ
dv/dt	Peak Diode Recovery dv/dt ③④	-5.0	V/ns
$T_J$	Operating Junction and	-55 to + 175	°C
$T_{STG}$	Storage Temperature Range		
	Soldering Temperature, for 10 seconds		
	Mounting torque, 6-32 or M3 screw	10 lbf•in (1.1N•m)	

### Thermal Resistance

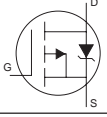
	Parameter	Typ.	Max.	Units
$R_{\theta JC}$	Junction-to-Case	—	1.4	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount)*	—	50	
$R_{\theta JA}$	Junction-to-Ambient**	—	110	

# IRFR/U5305PbF

## Electrical Characteristics @ T<sub>J</sub> = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V <sub>(BR)DSS</sub>	Drain-to-Source Breakdown Voltage	-55	—	—	V	V <sub>GS</sub> = 0V, I <sub>D</sub> = -250μA
ΔV <sub>(BR)DSS</sub> /ΔT <sub>J</sub>	Breakdown Voltage Temp. Coefficient	—	-0.034	—	V/°C	Reference to 25°C, I <sub>D</sub> = -1mA
R <sub>DS(on)</sub>	Static Drain-to-Source On-Resistance	—	—	0.065	Ω	V <sub>GS</sub> = -10V, I <sub>D</sub> = -16A ④
V <sub>GS(th)</sub>	Gate Threshold Voltage	-2.0	—	-4.0	V	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA
g <sub>fs</sub>	Forward Transconductance	8.0	—	—	S	V <sub>DS</sub> = -25V, I <sub>D</sub> = -16A⑥
I <sub>DSS</sub>	Drain-to-Source Leakage Current	—	—	-25	μA	V <sub>DS</sub> = -55V, V <sub>GS</sub> = 0V
		—	—	-250		V <sub>DS</sub> = -44V, V <sub>GS</sub> = 0V, T <sub>J</sub> = 150°C
I <sub>GSS</sub>	Gate-to-Source Forward Leakage	—	—	100	nA	V <sub>GS</sub> = 20V
	Gate-to-Source Reverse Leakage	—	—	-100		V <sub>GS</sub> = -20V
Q <sub>g</sub>	Total Gate Charge	—	—	63	nC	I <sub>D</sub> = -16A
Q <sub>gs</sub>	Gate-to-Source Charge	—	—	13		V <sub>DS</sub> = -44V
Q <sub>gd</sub>	Gate-to-Drain ("Miller") Charge	—	—	29		V <sub>GS</sub> = -10V, See Fig. 6 and 13 ④⑥
t <sub>d(on)</sub>	Turn-On Delay Time	—	14	—	ns	V <sub>DD</sub> = -28V
t <sub>r</sub>	Rise Time	—	66	—		I <sub>D</sub> = -16A
t <sub>d(off)</sub>	Turn-Off Delay Time	—	39	—		R <sub>G</sub> = 6.8Ω
t <sub>f</sub>	Fall Time	—	63	—		R <sub>D</sub> = 1.6Ω, See Fig. 10 ④⑥
L <sub>D</sub>	Internal Drain Inductance	—	4.5	—	nH	Between lead, 6mm (0.25in.) from package and center of die contact ⑤
L <sub>S</sub>	Internal Source Inductance	—	7.5	—		
C <sub>iss</sub>	Input Capacitance	—	1200	—	pF	V <sub>GS</sub> = 0V
C <sub>oss</sub>	Output Capacitance	—	520	—		V <sub>DS</sub> = -25V
C <sub>rss</sub>	Reverse Transfer Capacitance	—	250	—		f = 1.0MHz, See Fig. 5 ⑥

## Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I <sub>S</sub>	Continuous Source Current (Body Diode)	—	—	-31	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I <sub>SM</sub>	Pulsed Source Current (Body Diode) ①	—	—	-110		
V <sub>SD</sub>	Diode Forward Voltage	—	—	-1.3	V	T <sub>J</sub> = 25°C, I <sub>S</sub> = -16A, V <sub>GS</sub> = 0V ④
t <sub>rr</sub>	Reverse Recovery Time	—	71	110	ns	T <sub>J</sub> = 25°C, I <sub>F</sub> = -16A
Q <sub>rr</sub>	Reverse Recovery Charge	—	170	250	nC	di/dt = -100A/μs ④⑥

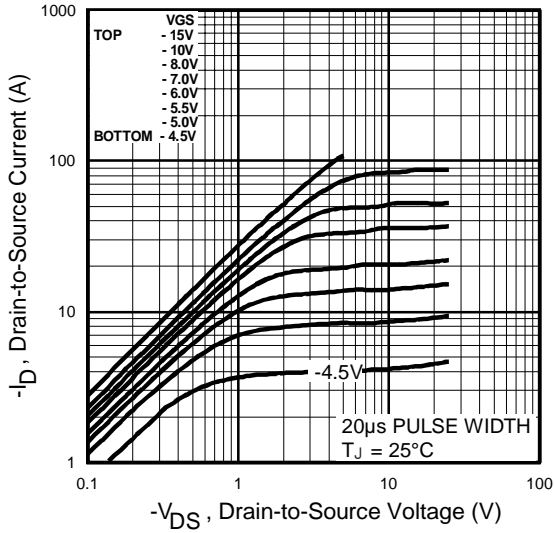
### Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See Fig. 11)
- ② V<sub>DD</sub> = -25V, starting T<sub>J</sub> = 25°C, L = 2.1mH  
R<sub>G</sub> = 25Ω, I<sub>AS</sub> = -16A. (See Figure 12)
- ③ I<sub>SD</sub> ≤ -16A, di/dt ≤ -280A/μs, V<sub>DD</sub> ≤ V<sub>(BR)DSS</sub>,  
T<sub>J</sub> ≤ 175°C
- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ This is applied for I-PAK, L<sub>S</sub> of D-PAK is measured between lead and center of die contact.
- ⑥ Uses IRF5305 data and test conditions.

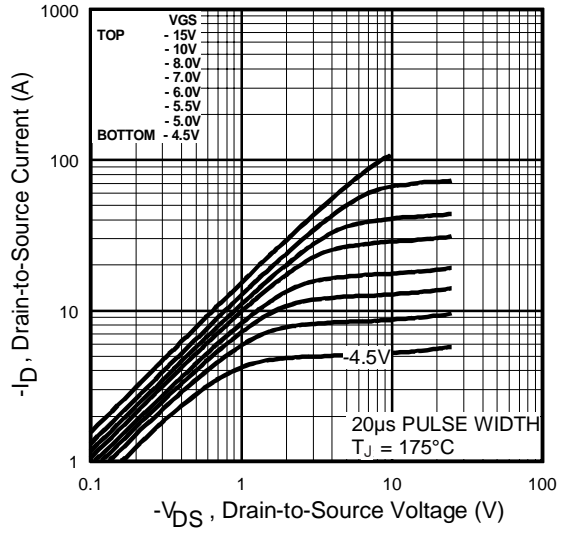
\* When mounted on 1" square PCB (FR-4 or G-10 Material).  
For recommended footprint and soldering techniques refer to application note #AN-994.

\*\* Uses typical socket mount.

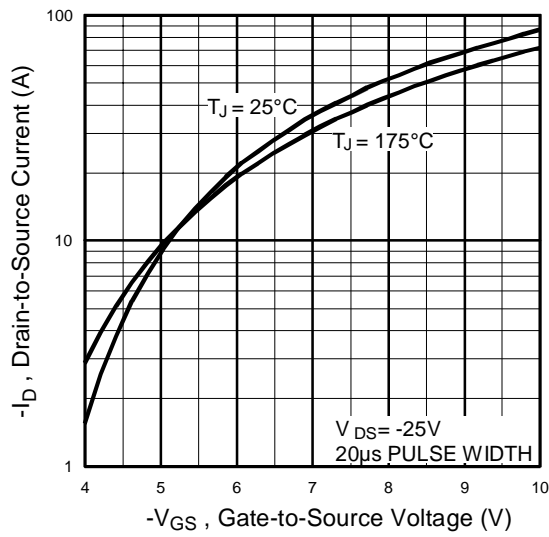
# IRFR/U5305PbF



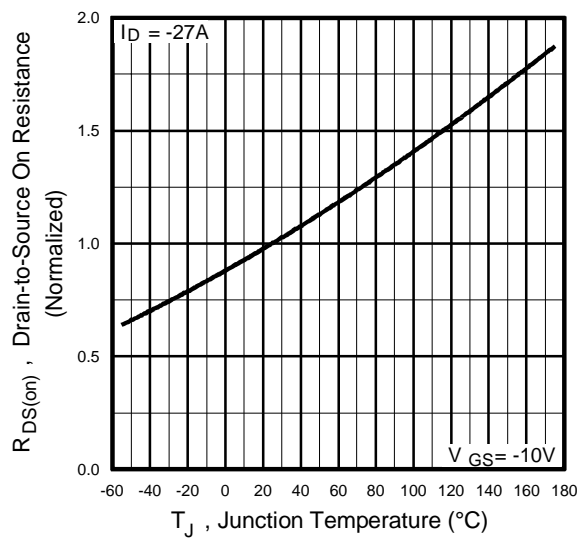
**Fig 1.** Typical Output Characteristics



**Fig 2.** Typical Output Characteristics

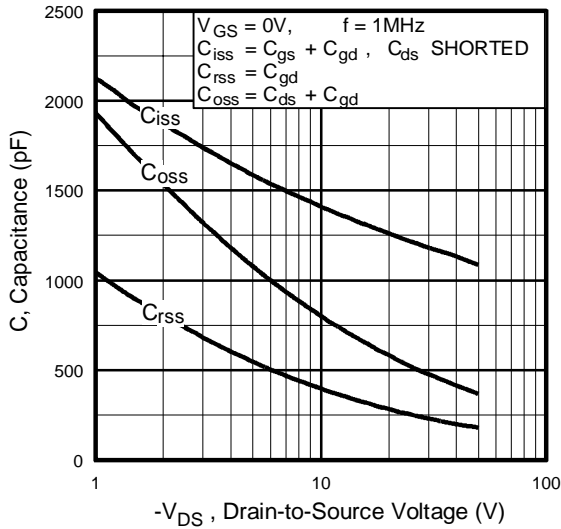


**Fig 3.** Typical Transfer Characteristics

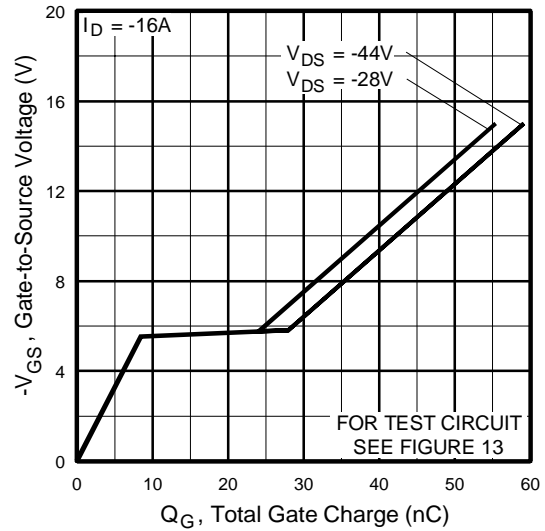


**Fig 4.** Normalized On-Resistance Vs. Temperature

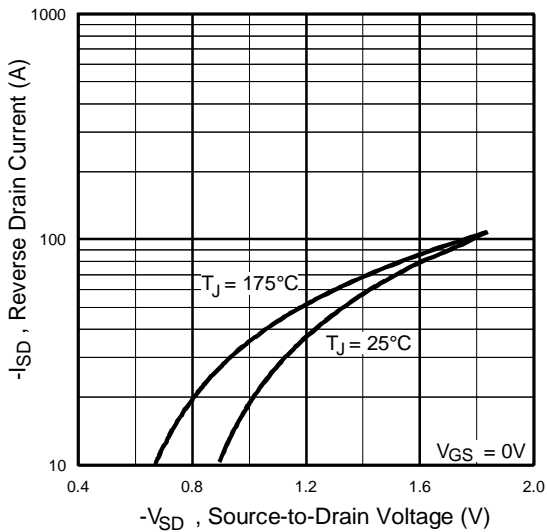
# IRFR/U5305PbF



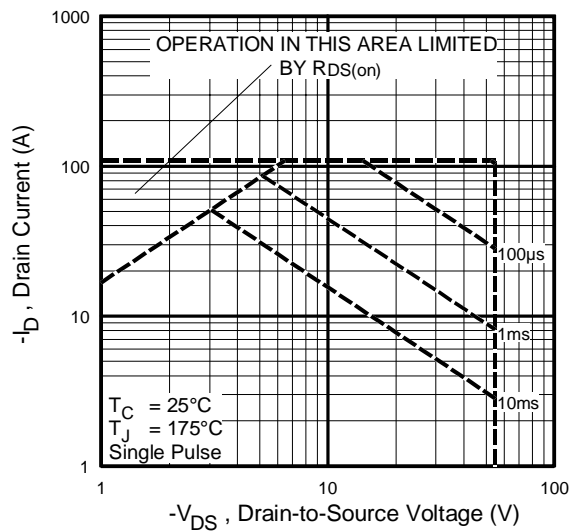
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage



**Fig 6.** Typical Gate Charge Vs. Gate-to-Source Voltage

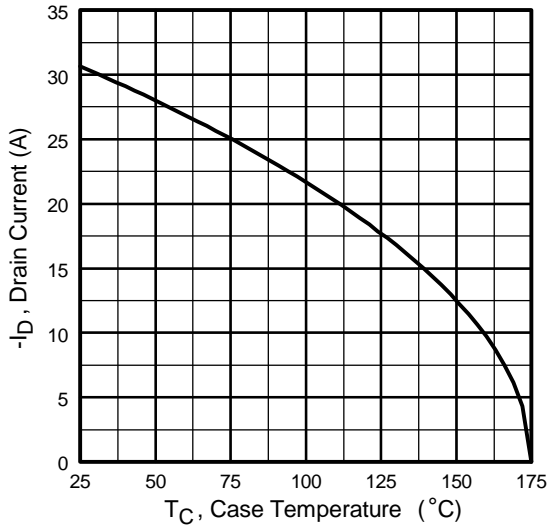


**Fig 7.** Typical Source-Drain Diode Forward Voltage

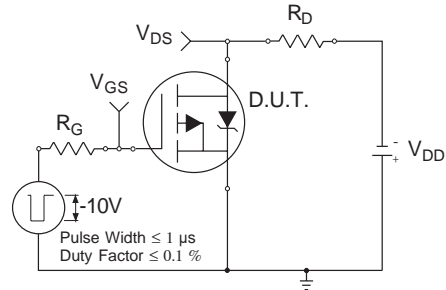


**Fig 8.** Maximum Safe Operating Area

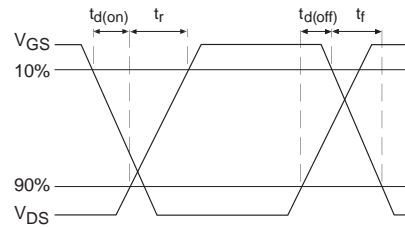
# IRFR/U5305PbF



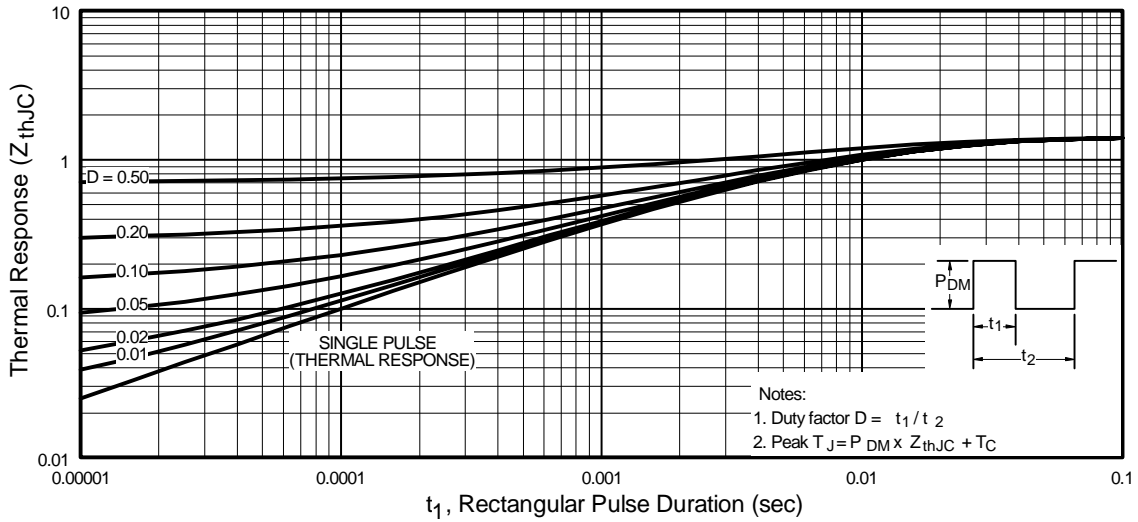
**Fig 9.** Maximum Drain Current Vs. Case Temperature



**Fig 10a.** Switching Time Test Circuit

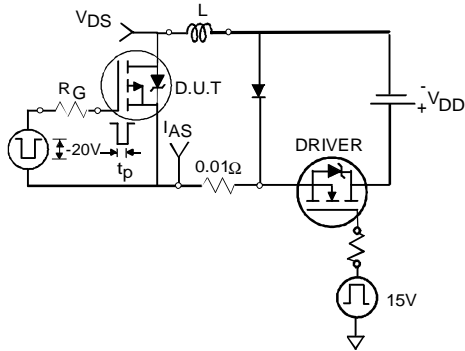


**Fig 10b.** Switching Time Waveforms

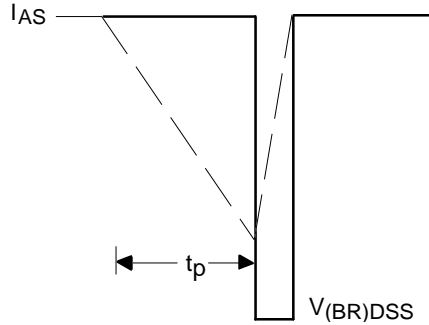


**Fig 11.** Maximum Effective Transient Thermal Impedance, Junction-to-Case

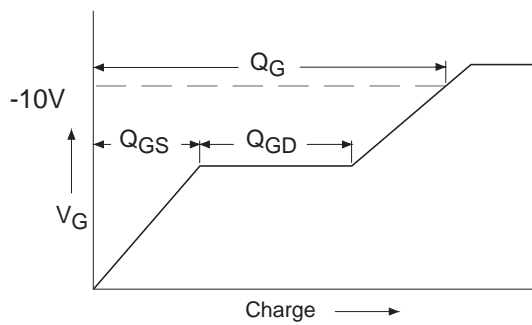
# IRFR/U5305PbF



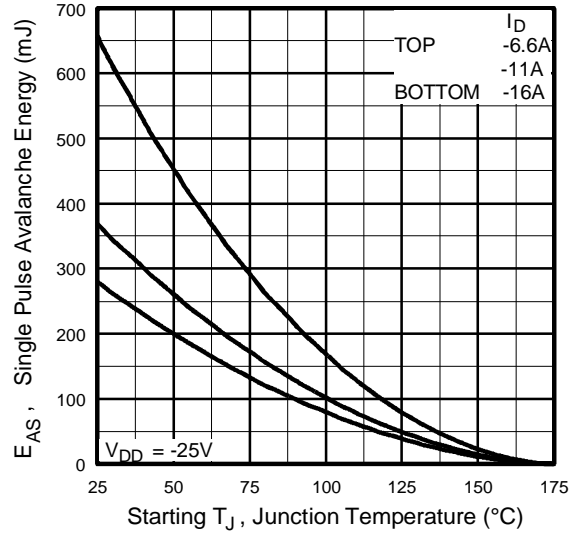
**Fig 12a.** Unclamped Inductive Test Circuit



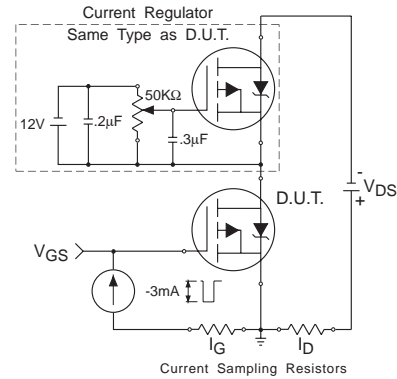
**Fig 12b.** Unclamped Inductive Waveforms



**Fig 13a.** Basic Gate Charge Waveform



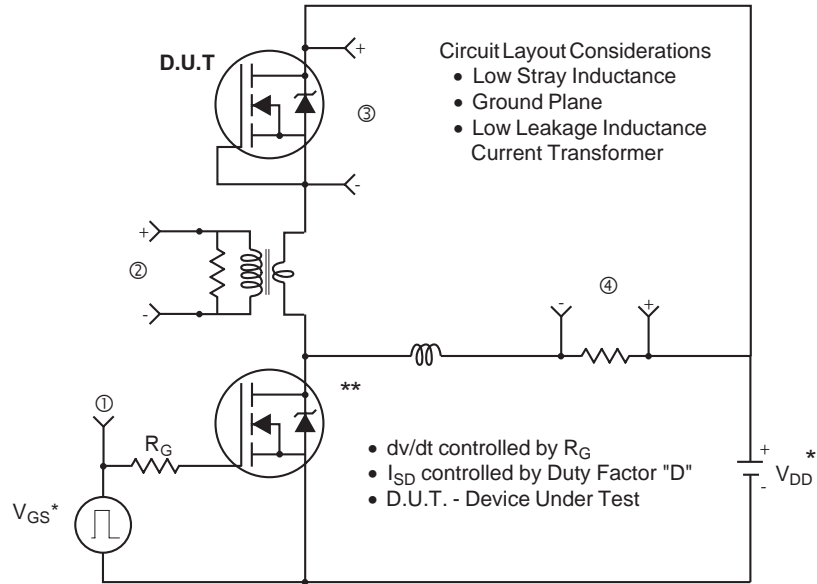
**Fig 12c.** Maximum Avalanche Energy Vs. Drain Current



**Fig 13b.** Gate Charge Test Circuit

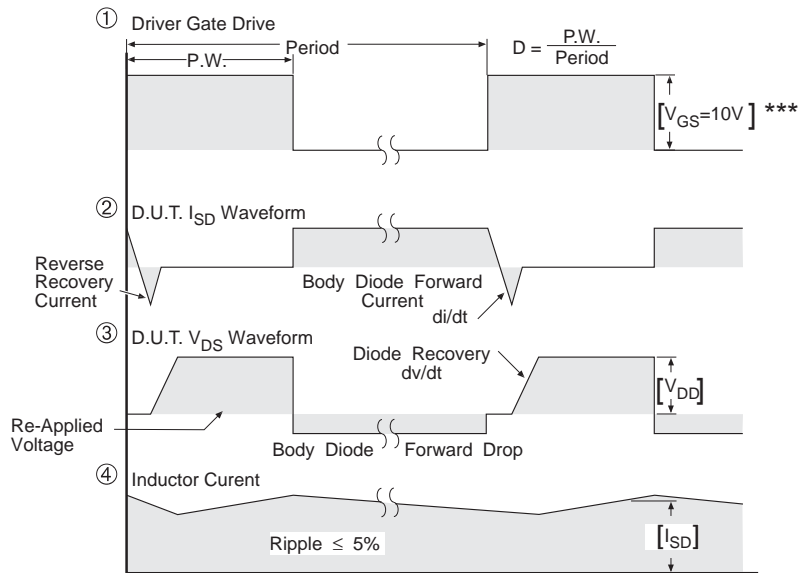
# IRFR/U5305PbF

## Peak Diode Recovery dv/dt Test Circuit



\* Reverse Polarity for P-Channel

\*\* Use P-Channel Driver for P-Channel Measurements



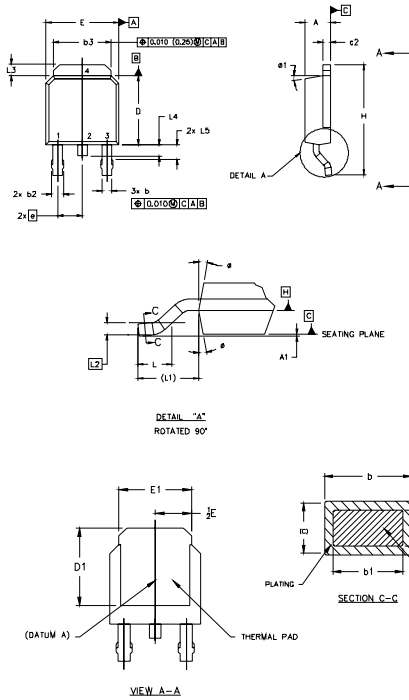
\*\*\*  $V_{GS} = 5.0V$  for Logic Level and 3V Drive Devices

**Fig 14.** For P-Channel HEXFETS

# IRFR/U5305PbF

## D-Pak (TO-252AA) Package Outline

Dimensions are shown in millimeters (inches)



- NOTES:
- 1.0 DIMENSIONING AND TOLERANCING PER ASME Y14.5 M- 1994.
  - 2.0 DIMENSIONS ARE SHOWN IN INCHES [MILLIMETERS]
  - 3.0 LEAD DIMENSION UNCONTROLLED IN L5
  - 4.0 DIMENSION D1 AND E1 ESTABLISH A MINIMUM MOUNTING SURFACE FOR THERMAL PAD.
  - 5.0 SECTION C-C DIMENSIONS APPLY TO THE FLAT SECTION OF THE LEAD BETWEEN .005 [0.127] AND .010 [0.2540] FROM THE LEAD TIP.
  - 6.0 DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
  - 7.0 OUTLINE CONFORMS TO JEDEC OUTLINE TO-252AA.

SYMBOL	MILLIMETERS		INCHES		NOTES
	MIN.	MAX.	MIN.	MAX.	
A	2.18	2.39	.086	.094	
A1		0.13		.005	
b	0.64	0.89	.025	.035	5
b1	0.64	0.79	.025	0.031	5
b2	0.76	1.14	.030	.045	
b3	4.95	5.46	.195	.215	
c	0.46	0.61	.018	.024	5
c1	0.41	0.56	.016	.022	5
c2	.046	0.89	.018	.035	5
D	5.97	6.22	.235	.245	6
D1	5.21	-	.205	-	4
E	6.35	6.73	.250	.265	6
E1	4.32	-	.170	-	4
e	2.29	-	.090 BSC	-	
H	9.40	10.41	.370	.410	
L	1.40	1.78	.055	.070	
L1	2.74 REF.	-	.108 REF.	-	
L2	0.051 BSC	-	.020 BSC	-	
L3	0.89	1.27	.035	.050	
L4		1.02		.040	
L5	1.14	1.52	.045	.060	3
a	0"	10"	0"	10"	
a1	0"	15"	0"	15"	

### LEAD ASSIGNMENTS

- HEXFEEI
- 1.- GATE
  - 2.- DRAIN
  - 3.- SOURCE
  - 4.- DRAIN

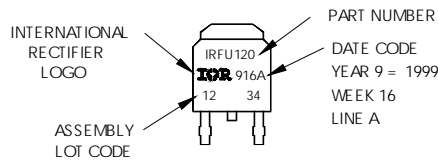
### IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

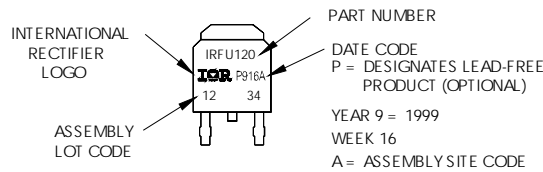
## D-Pak (TO-252AA) Part Marking Information

EXAMPLE: THIS IS AN IRFR120  
WITH ASSEMBLY  
LOT CODE 1234  
ASSEMBLED ON WW 16, 1999  
IN THE ASSEMBLY LINE "A"

Note: "P" in assembly line position  
indicates "Lead-Free"



OR



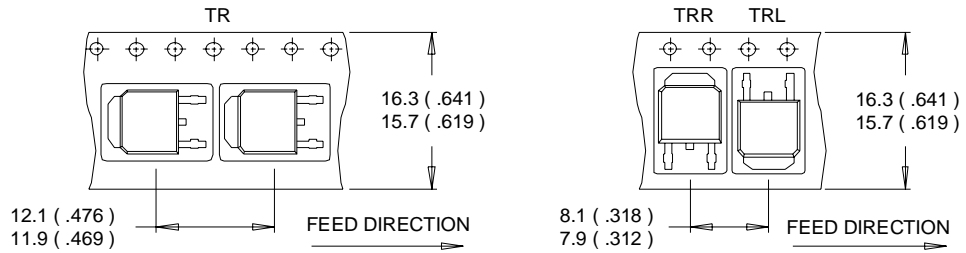




# IRFR/U5305PbF

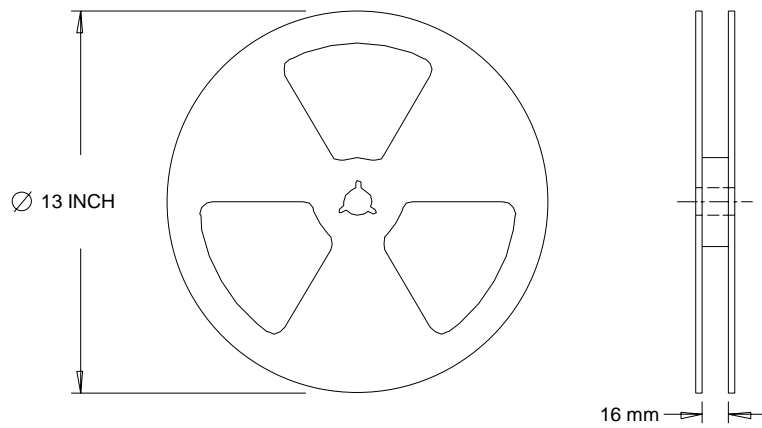
## D-Pak (TO-252AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS ( INCHES ).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



NOTES :

1. OUTLINE CONFORMS TO EIA-481.

Data and specifications subject to change without notice.

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